

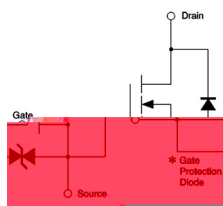
Rev.H Sep.-2019

SOT-23 N MOS N- CHANNEL MOSFET in a SOT-23 Plastic Package.

500V HBM

Low on-resistance, fast switching speed, low voltage drive, easily designed drive circuits, easy to parallel. ESD protected up to 500V HBM .

Interfacing, switching.



PIN1 G PIN 2 S PIN 3 D

Marking

KL

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current – Continuous	I_D	100	mA
Drain Current- Pulsed	I_{DP}^{*1}	400	mA
Reverse Drain Current – Continuous	I_{DR}	100	mA
Reverse Drain Current –Pulsed	I_{DRP}^{*1}	200	mA
Total Power Dissipation	P_D^{*2}	250	mW
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	-55 150	

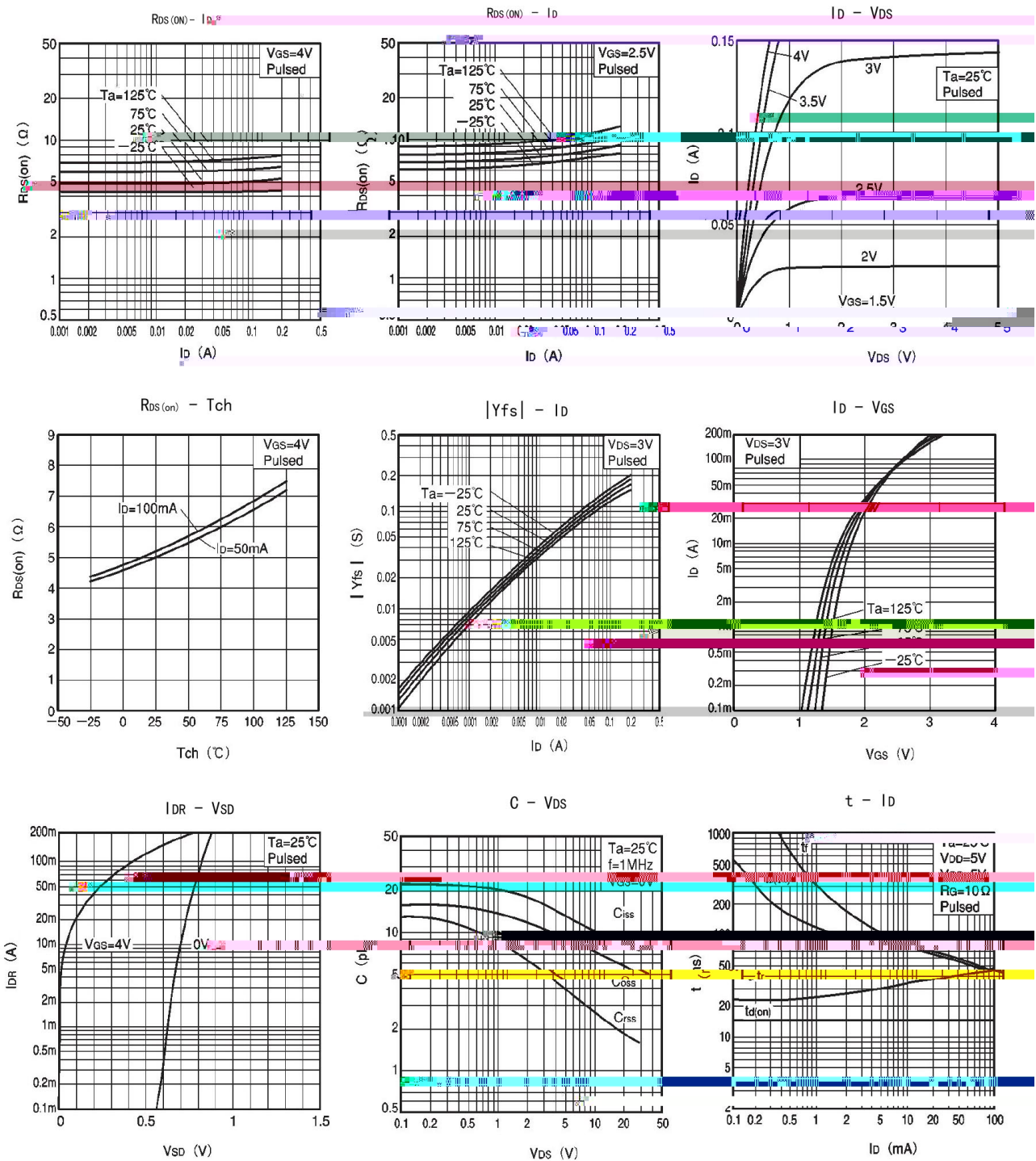
*1: $P_w \leq 10 \mu s$, Duty cycle $\leq 1\%$

*2: With each pin mounted on the recommended lands

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain–Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V$ $I_D=10\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=3.0V$ $I_D=100\mu A$	0.8		1.5	V

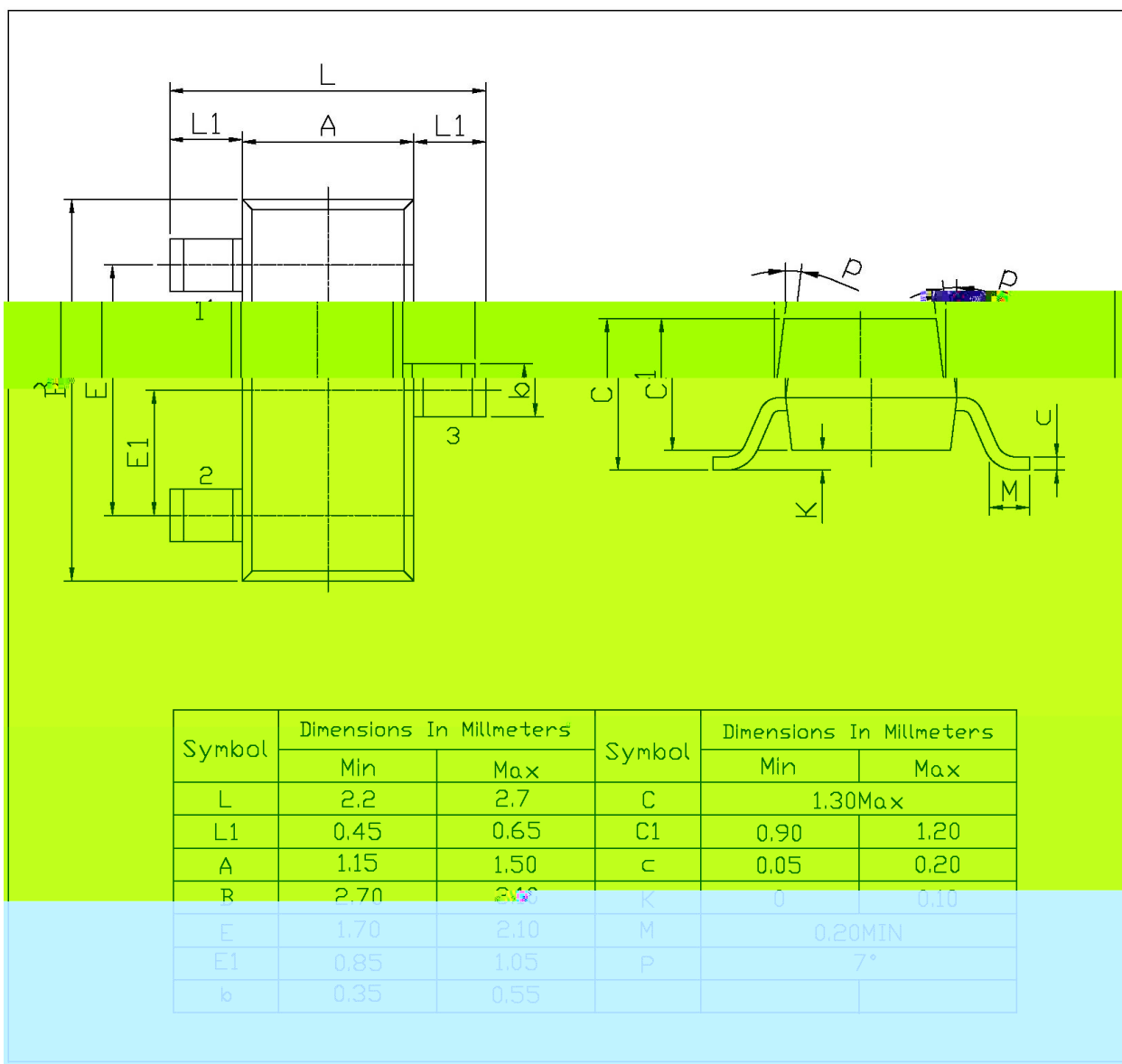
Static Drain–Source
On–Resistance

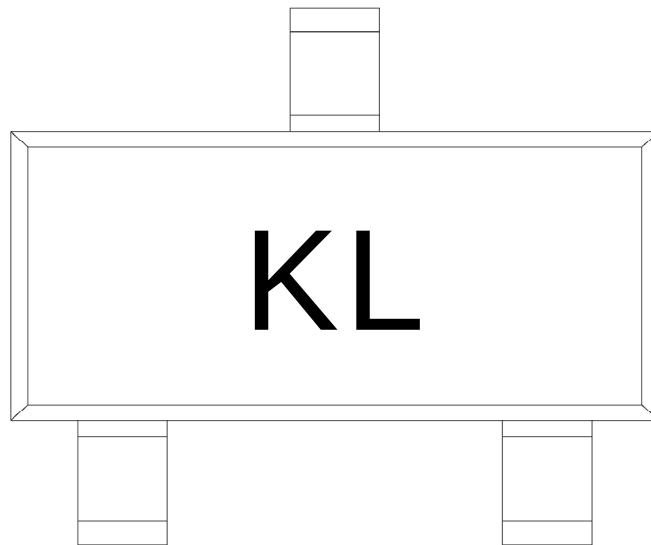
R



SOT-23

单位; mm

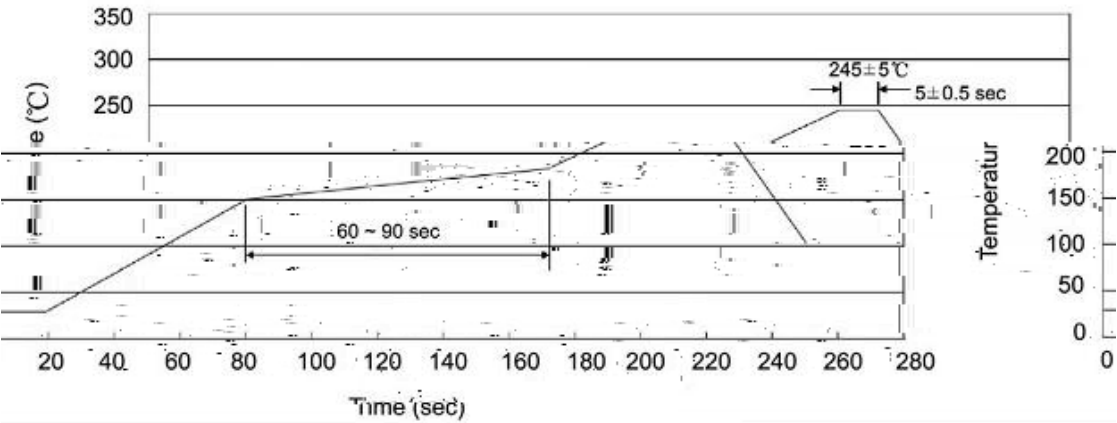




KL:

Note:

KL Package Type



Note:

- 1

150 180

60 90sec;
- 2

245±5

5±0.5sec;
- 3

2 10

/sec.
- 1.Preheating:150~180

, Time:60~90sec.
- 2.Peak Temp.:245±5

, Duration:5±0.5sec.
3. Cooling Speed: 2~10

/sec.

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱